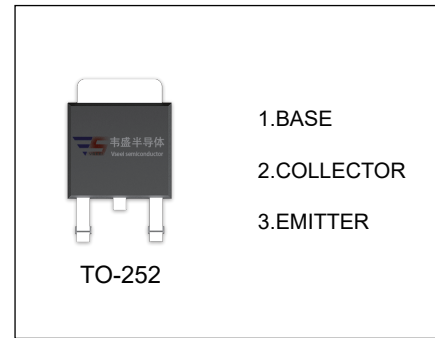


## 2SD1899 TRANSISTOR (NPN)

### FEATURES

- LOW  $V_{CE(sat)}$
- High Transition Frequency



### MAXIMUM RATINGS ( $T_a=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
$V_{CBO}$	Collector-Base Voltage	60	V
$V_{CEO}$	Collector-Emitter Voltage	60	V
$V_{EBO}$	Emitter-Base Voltage	7	V
$I_C$	Collector Current	3	A
$P_C$	Collector Power Dissipation	1	W
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	125	$^\circ\text{C/W}$
$T_J, T_{stg}$	Operation Junction and Storage Temperature Range	-55~+150	$^\circ\text{C}$

### ELECTRICAL CHARACTERISTICS ( $T_a=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu\text{A}, I_E=0$	60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1\text{mA}, I_B=0$	60			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu\text{A}, I_C=0$	7			V
Collector cut-off current	$I_{CBO}$	$V_{CB}=60\text{V}, I_E=0$			10	$\mu\text{A}$
Emitter cut-off current	$I_{EBO}$	$V_{EB}=7\text{V}, I_C=0$			10	$\mu\text{A}$
DC current gain	$h_{FE(1)}$	$V_{CE}=2\text{V}, I_C=0.2\text{A}$	60			
	$h_{FE(2)}$	$V_{CE}=2\text{V}, I_C=0.6\text{A}$	100		400	
	$h_{FE(3)}$	$V_{CE}=2\text{V}, I_C=2\text{A}$	50			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=1.5\text{A}, I_B=0.15\text{A}$			0.25	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=1.5\text{A}, I_B=0.15\text{A}$			1.2	V
Collector output capacitance	$C_{ob}$	$V_{CB}=10\text{V}, I_E=0, f=1\text{MHz}$		30		pF
Transition frequency	$f_T$	$V_{CE}=5\text{V}, I_C=1.5\text{A}$		120		MHz

\*Pulse test: pulse width  $\leq 350\mu\text{s}$ , duty cycle  $\leq 2.0\%$ .

### CLASSIFICATION OF $h_{FE(2)}$

RANK	M	L	K
RANGE	100-200	160-320	200-400

